



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



## Thyristor Modules Thyristor/Diode Modules

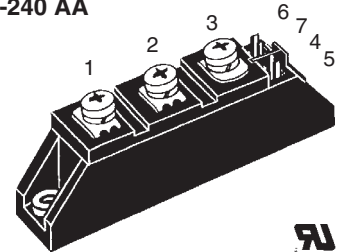
$$I_{TRMS} = 2 \times 180 \text{ A}$$

$$I_{TAVM} = 2 \times 115 \text{ A}$$

$$V_{RRM} = 800-1800 \text{ V}$$

$V_{RSM}$	$V_{RRM}$	Type					
$V_{DSM}$	$V_{DRM}$	Version			Version		
V	V	1 B	8 B	1 B	8 B	1 B	8 B
900	800	MCC 72-08	io1 B / io8 B	MCD 72-08	io1 B / io8 B		
1300	1200	MCC 72-12	io1 B / io8 B	MCD 72-12	io1 B / io8 B		
1500	1400	MCC 72-14	io1 B / io8 B	MCD 72-14	io1 B / io8 B		
1700	1600	MCC 72-16	io1 B / io8 B	MCD 72-16	io1 B / io8 B		
1900	1800	MCC 72-18	io1 B / io8 B	MCD 72-18	io1 B / io8 B		

TO-240 AA

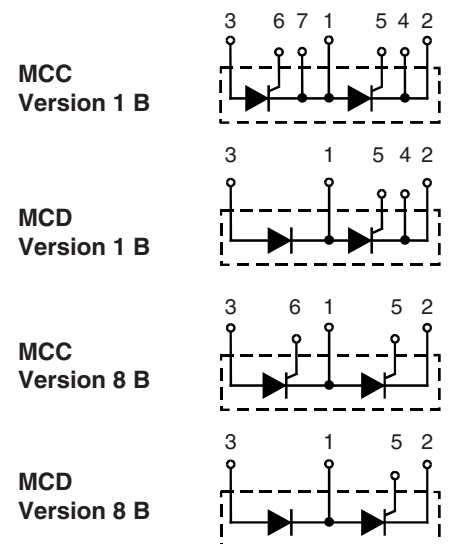


Symbol	Conditions	Maximum Ratings	
$I_{TRMS}, I_{FRMS}$ $I_{TAVM}, I_{FAVM}$	$T_{VJ} = T_{VJM}$ $T_C = 63^\circ\text{C}; 180^\circ \text{ sine}$ $T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	180 115 85	A A A
$I_{TSM}, I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	A A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	A A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	$14\ 450$ $13\ 500$ $A^2s$ $A^2s$
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	$11\ 850$ $11\ 300$ $A^2s$ $A^2s$
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}; t_p = 200 \mu\text{s}$	repetitive, $I_T = 250 \text{ A}$	150 A/ $\mu\text{s}$
	$V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.45 \text{ A}$ $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	non repetitive, $I_T = I_{TAVM}$	500 A/ $\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM};$ $R_{GK} = \infty; \text{method 1 (linear voltage rise)}$	$V_{DR} = \frac{2}{3} V_{DRM}$	1000 V/ $\mu\text{s}$
$P_{GM}$	$T_{VJ} = T_{VJM};$ $I_T = I_{TAVM};$	$t_p = 30 \mu\text{s}$ $t_p = 300 \mu\text{s}$	10 5 W W
$P_{GAV}$			0.5 W
$V_{RGM}$			10 V
$T_{VJ}$			-40...+125 $^\circ\text{C}$
$T_{VJM}$			125 $^\circ\text{C}$
$T_{stg}$			-40...+125 $^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA};$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 3600 V~ V~
$M_d$	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 2.5-4.0/22-35 Nm/lb.in. Nm/lb.in.
Weight	Typical including screws		90 g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions

© 2004 IXYS All rights reserved



### Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded  $\text{Al}_2\text{O}_3$  -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Gate-cathode twin pins for version 1B

### Applications

- DC motor control
- Softstart AC motor controller
- Light, heat and temperature control

### Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling
- Reduced protection circuits



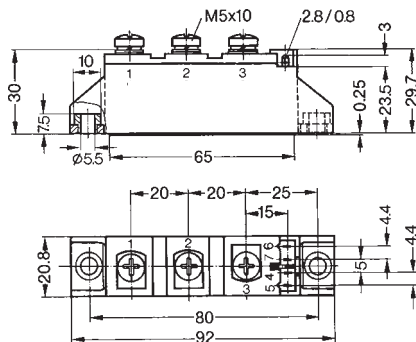
Symbol	Conditions	Characteristic Values
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	5 mA
$V_T / V_F$	$I_T / I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.74 V
$V_{T0}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.85 V
$r_T$		3.2 mΩ
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	2.5 V
	$T_{VJ} = -40^\circ\text{C}$	2.6 V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	150 mA
	$T_{VJ} = -40^\circ\text{C}$	200 mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	0.2 V
$I_{GD}$		10 mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450 mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200 mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2 μs
$t_q$	$T_{VJ} = T_{VJM}; I_T = 150 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = \frac{2}{3} V_{DRM}$	typ. 185 μs
$Q_S$	$T_{VJ} = T_{VJM}; I_T / I_F = 50 \text{ A}, -di/dt = 6 \text{ A}/\mu\text{s}$	170 μC
$I_{RM}$		45 A
$R_{thJC}$	per thyristor/diode; DC current per module	0.3 K/W
$R_{thJK}$	per thyristor/diode; DC current per module	0.15 K/W
	other values see Fig. 8/9	0.5 K/W
		0.25 K/W
$d_s$	Creepage distance on surface	12.7 mm
$d_A$	Strike distance through air	9.6 mm
$a$	Maximum allowable acceleration	50 m/s <sup>2</sup>

Optional accessories for module-type MCC 72 version 1 B

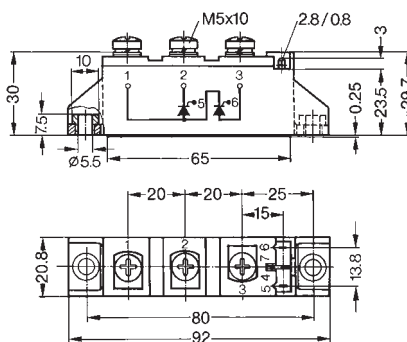
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red  
 Type **ZY 200L** (L = Left for pin pair 4/5) } UL 758, style 1385,  
 Type **ZY 200R** (R = right for pin pair 6/7) } CSA class 5851, guide 460-1-1

Dimensions in mm (1 mm = 0.0394")

### MCC / MCD Version 1 B



### MCC Version 8 B



### MCD Version 8 B

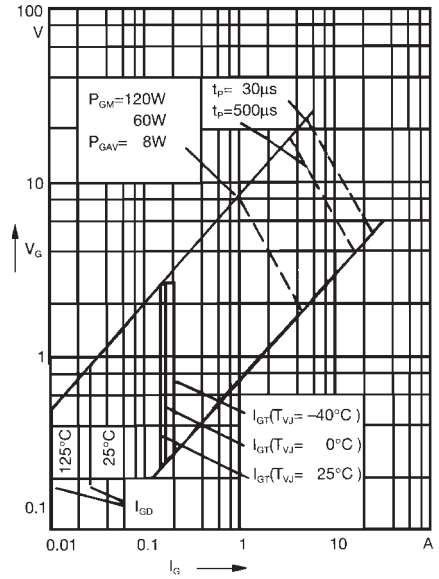
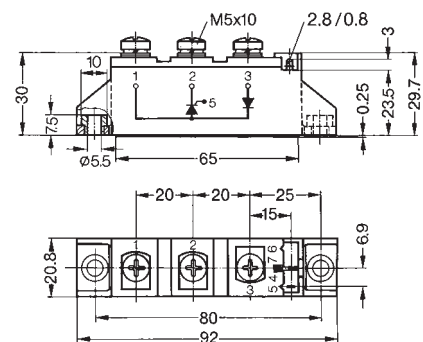


Fig. 1 Gate trigger characteristics

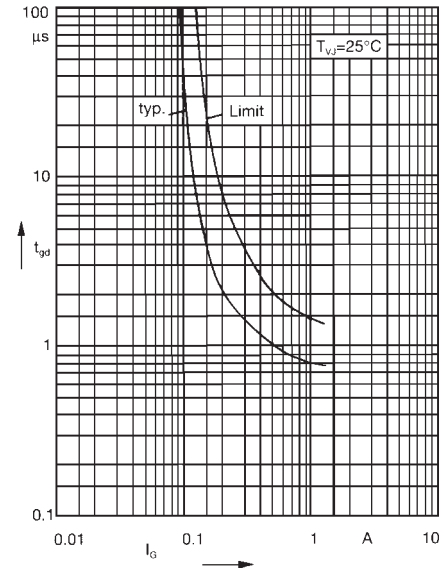
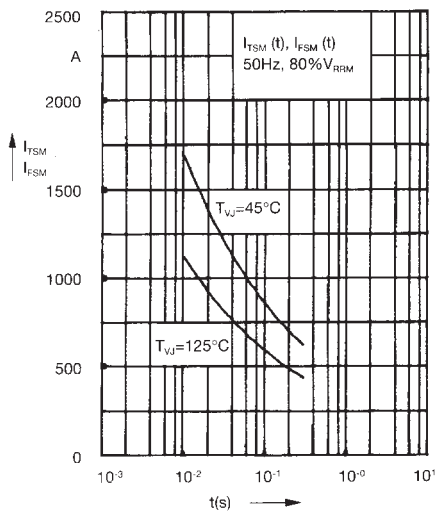
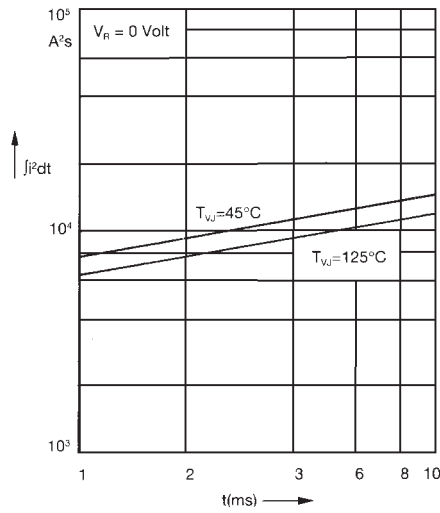


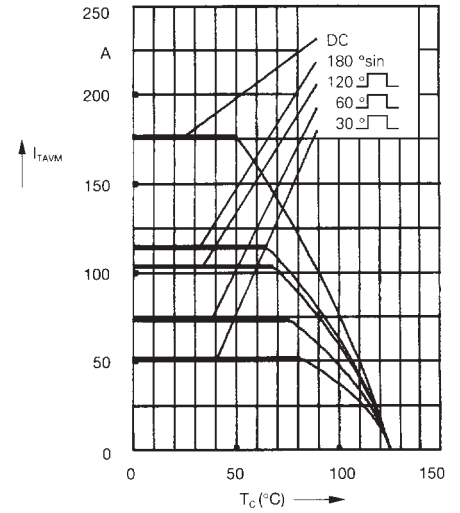
Fig. 2 Gate trigger delay time



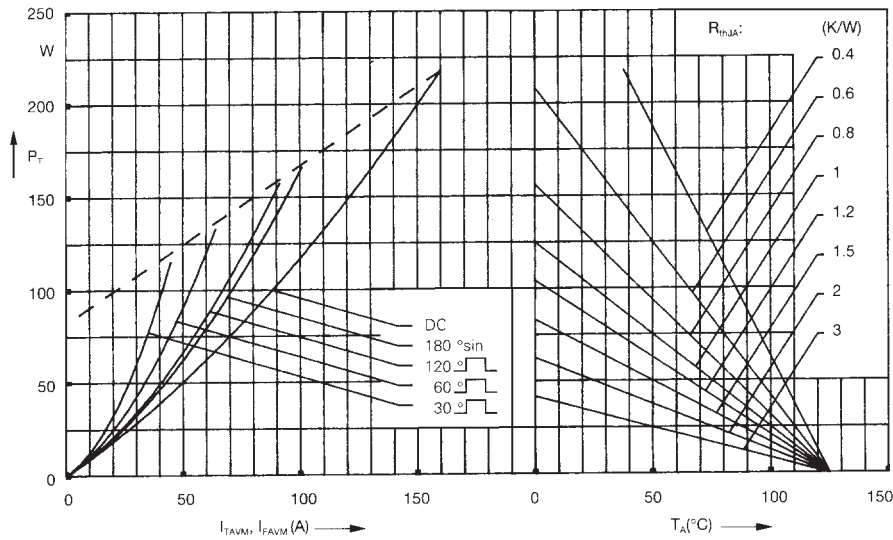
**Fig. 3 Surge overload current**  
 $I_{TSM}$ ,  $I_{FSM}$ : Crest value, t: duration



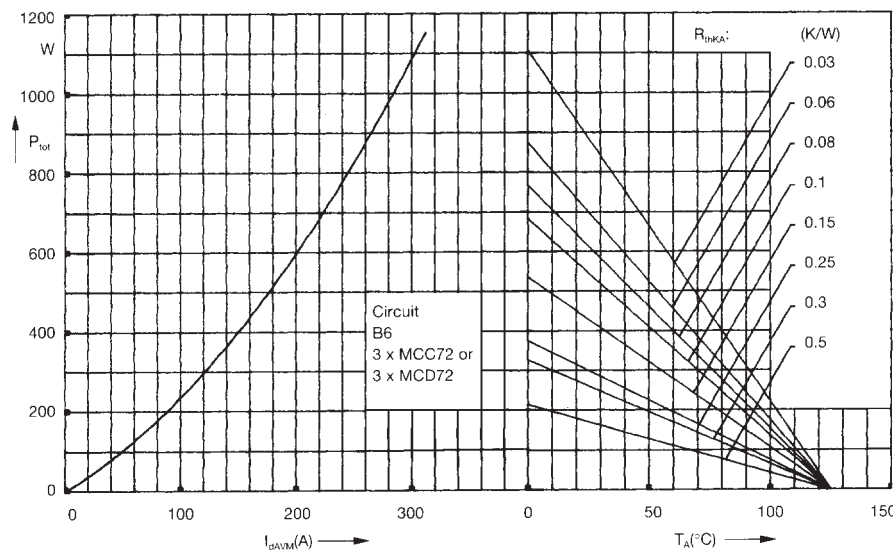
**Fig. 4  $\int i^2 dt$  versus time (1-10 ms)**



**Fig. 4a Maximum forward current at case temperature**



**Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)**



**Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature**

IXYS reserves the right to change limits, test conditions and dimensions

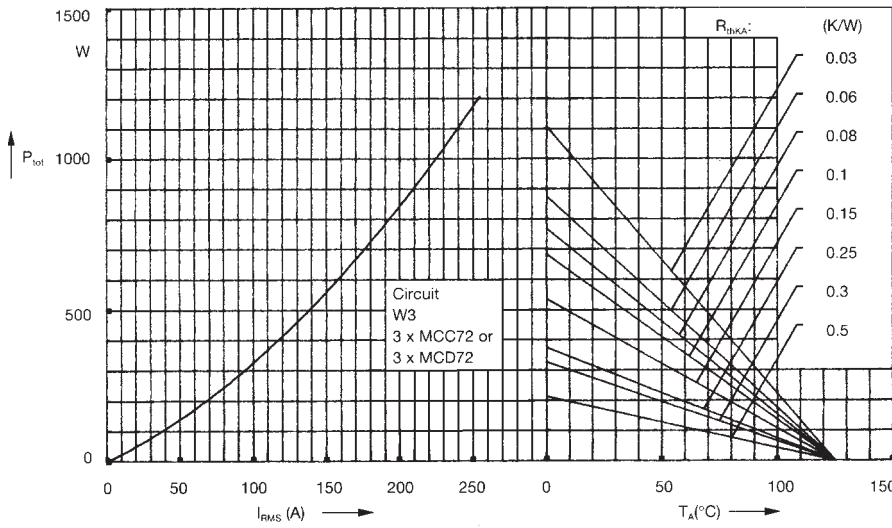


Fig. 7 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

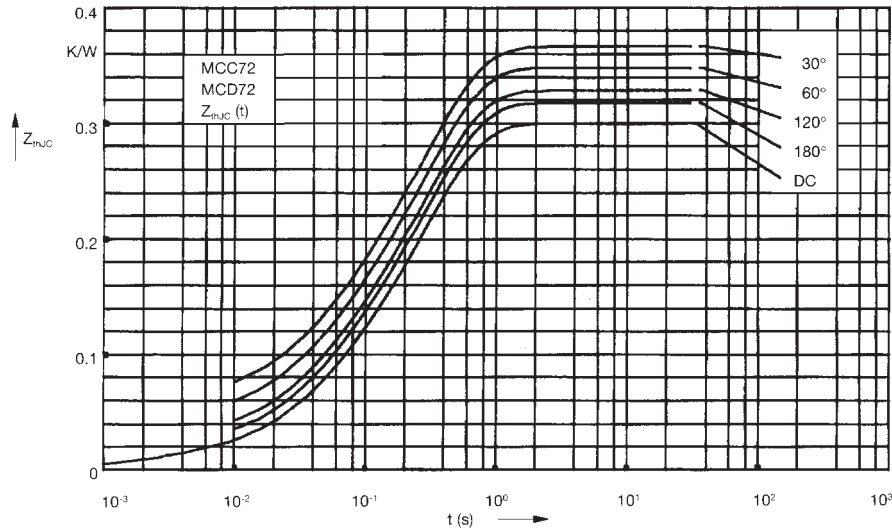


Fig. 8 Transient thermal impedance junction to case (per thyristor or diode)

$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.3
180°	0.31
120°	0.33
60°	0.35
30°	0.37

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3

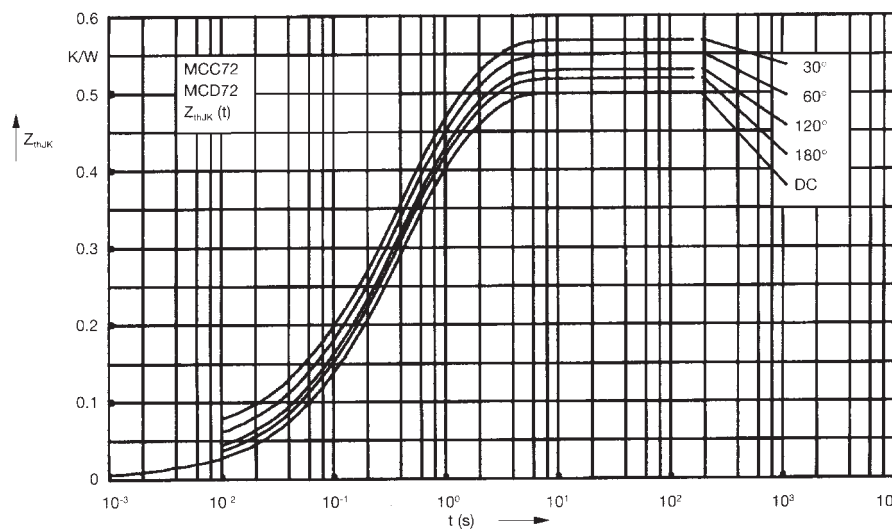


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor or diode)

$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ (K/W)
DC	0.5
180°	0.51
120°	0.53
60°	0.55
30°	0.57

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.008	0.0019
2	0.054	0.047
3	0.238	0.3
4	0.2	1.25